No. of Printed Pages: 3

BIEL-001

B.Tech. (BTCSVI / BTECVI / BTELVI)

Term-End Examination

June, 2016

BIEL-001 : BASICS OF ELECTRONICS ENGINEERING

Time : 3 hours

10366

Maximum Marks: 70

Note : Attempt any **seven** questions. All questions carry equal marks. Use of scientific calculator is allowed.

- What is doping of a semiconductor ? Explain how P and N-type semiconductors are formed. Also draw their energy band diagrams clearly showing the different energy levels.
- 2. (a) What are intrinsic and extrinsic semiconductors? Comment on the conductivity of extrinsic semiconductors.
 - (b) The resistivity of a doped silicon material is 9×10^3 ohm-m. The Hall coefficient is 3.6×10^{-4} m³ coulomb⁻¹. Assuming single carrier conduction, find the mobility and density of charge carriers (e = 1.6×10^{-19} Coulomb).

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 3. (a) Sketch the volt - ampere characteristics of a Zener diode. Indicate the knee on the curve and explain its significance. What happens when the current in Zener decreases below the knee current? (b) What do you mean by drift and diffusion current? 3 4. (a) What is an ideal diode ? Sketch the characteristics of an ideal diode. (b) Explain the diffusion and depletion layer capacitance of a P-N junction. 5. Draw a neat sketch to illustrate the structure of N-channel JFET. Explain its principle of operation. 6. (a) Describe the basic principles of phototransistors. (b) Draw the circuits of the various transistor configuration mostly used ? Give its typical uses. 7. (a) Compare PMOS and CMOS transistors. (b) Explain briefly 'semiconductor heterojunctions' and their transit time effect. 5 				
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BIEL-001 2		(b)	Explain briefly 'semiconductor heterojunctions' and their transit time effect.	5
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- Why are filters used along with rectifiers in the 8. construction of a power supply ? List the filter types used in power supplies. Explain their effect on rectifier output waveforms.
- A half-wave rectifier has a load resistance of 9. $3.5 \text{ k}\Omega$. If the diode and secondary of the transformer have a total resistance of 800 k Ω and the AC input voltage has 240 V (peak value), determine
 - peak, rms and average values of current **(a)** through load.
 - DC power output, (b)
 - (c) AC power input, and
 - rectification efficiency. (d)
- of the 10. Write short notes two on anv following: $2 \times 5 = 10$
 - Voltage Regulator (a)
 - (b) Varactor Diode
 - Elbers-Moll Model for N-P-N Transistors (c)

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